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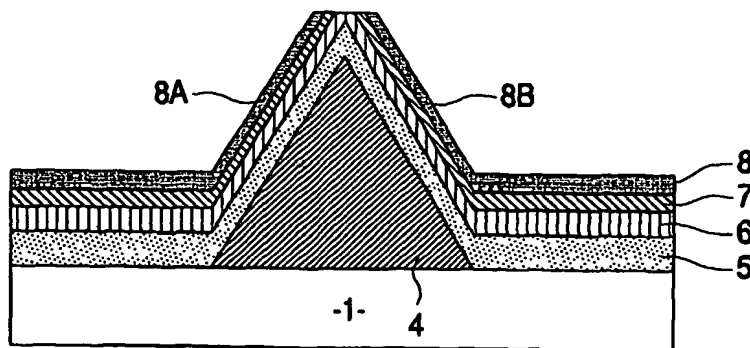
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(54) Title: THIN FILM TRANSISTOR



(57) Abstract: A method of fabricating a TFT comprises: etching a base layer structure (9) on a substrate (1) so as to form a gate (4) with inclined side edges (4a, 4b) that extend towards an apex region (12) with a tip (13) of a radius of a few nanometers, depositing an amorphous silicon channel layer (6) over the inclined side edges and the apex region, depositing a metal layer (8) over the channel layer so as to cover the apex region and the side edges, applying a layer of masking material (14) over the conductive material and selectively etching it so that the metal layer (8) in the apex region protrudes

through and upstands from the masking material, and selectively etching the metal (8) that protrudes through the masking material (14) in the apex region such as to provide separate, self aligned source and drain regions (8a, 8b) overlying the inclined edges with a short channel (L) between them.